

MARKED-UP VERSION OF THE CLAIMS:

18. (Amended) A trench capacitor comprising:

a crystalline silicon substrate including deep trenches having surfaces in the substrate substantially free of native oxide; and

a dielectric stack, including a continuous monocrystalline silicon nitride layer, formed on the surfaces of the trenches, the dielectric stack for forming a node dielectric between electrodes of the trench capacitor.

23. (Amended) A trench capacitor comprising:

a crystalline silicon substrate including a trench having a surface formed in the substrate, the surface being substantially free of native oxide;

a continuous monocrystalline silicon nitride layer, formed on the surface of the trench; and

an amorphous silicon nitride layer formed on the crystalline silicon nitride layer, the crystalline silicon nitride layer and the amorphous silicon nitride layer for forming a dielectric between electrodes.



PATENT

GAU 2812

Express Mail Label No.:

Case Docket No.: 99 P 7722 US 01 (2055-98)

Date: August 9, 2001

ASSISTANT COMMISSIONER FOR PATENTS
Washington, D.C. 20231
Box PATENT APPLICATION

09/594,638

RECEIVED
AUG 17 2001
TECHNOLOGY CENTER 2800

Sir:

Transmitted herewith is an amendment in the identified application noted below.

☒ No additional fee is required.

In re application of:

Serial No.: Jammy et al.

Filed: June 15, 2000

For: **METHOD FOR FORMING CRYSTALLINE SILICON NITRIDE**

The filing fee has been calculated as shown below:

	(Col. 1)	(Col. 2)	(Col. 3)	OTHER THAN A SMALL ENTITY FEE	
CLAIMS	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE	ADDIT. FEE
TOTAL	<u>12</u>	MINUS <u>12</u>	= <u>20</u> x 18 =	\$ <u>0</u>	
INDEP	<u>3</u>	MINUS <u>3</u>	= <u>20</u> x 18 =	\$ <u>0</u>	
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM				+ 270 =	\$0

TOTAL \$ 0☒ Please charge my Deposit Account No. 19-2179 in the amount of \$ 0☐ A duplicate copy of this sheet is enclosed.☐ A check in the amount of \$ is attached.☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 19-2179.
☐ A duplicate copy of this sheet is enclosed.☒ Any additional filing fees required under 37 CFR 1.16 for the presentation of excess claims.☒ Any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

Stanton C. Braden
Registration No. 32,556
Attorney for Applicant

Date: 8/8/01

Infinion Technologies North America Corp.
c/o Siemens Corporation
186 Wood Avenue South
Iselin, NJ 08830
Tel: (732) 321-3150